Unit: mm

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA1955

General Purpose Amplifier Applications Switching and Muting Switch Application

• Low saturation voltage: VCE (sat) (1) = -15 mV (typ.) @IC = -10 mA/IB = -0.5 mA

• Large collector current: IC = -400 mA (max)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-15	V
Collector-emitter voltage	V _{CEO}	-12	٧
Emitter-base voltage	V _{EBO}	-5	٧
Collector current	IC	-400	mA
Base current	ΙΒ	-50	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.

1. BASE
2. EMITTER
3. COLLECTOR

JEDEC

JEITA

TOSHIBA

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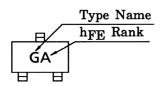
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Weight: 2.4 mg (typ.)

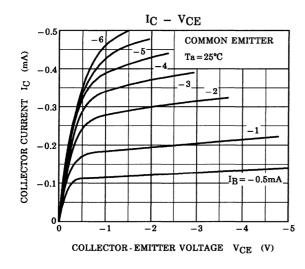
operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

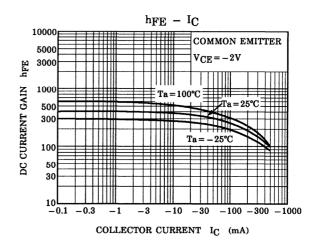
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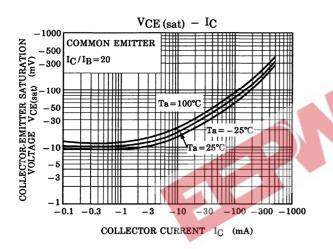


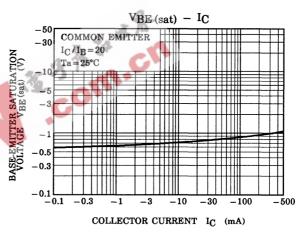
Electrical Characteristics (Ta = 25°C)

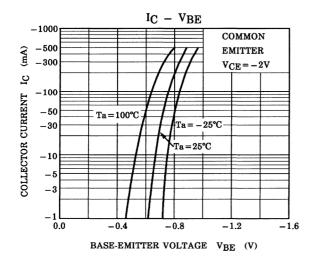
Chara	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off co	urrent	I _{CBO}	V _{CB} = -15 V, I _E = 0	_	_	-0.1	μА	
Emitter cut-off cur	rent	I _{EBO}	$V_{EB} = -5 \text{ V}, I_{C} = 0$	_	_	-0.1	μА	
DC current gain		h _{FE} (Note)	$V_{CE} = -2 \text{ V, I}_{C} = -10 \text{ mA}$	300	_	1000		
Collector-emitter saturation voltage		V _{CE} (sat) (1)	$I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$	_	-15	-30	mV	
		V _{CE} (sat) (2)	$I_C = -200 \text{ mA}, I_B = -10 \text{ mA}$	_	-110	-250	IIIV	
Base-emitter satu	ration voltage	V _{BE} (sat)	$I_C = -200 \text{ mA}, I_B = -10 \text{ mA}$	_	-0.87	-1.2	V	
Transition frequen	су	f _T	$V_{CE} = -2 \text{ V}, I_{C} = -10 \text{ mA}$	80	130	_	MHz	
Collector output ca	apacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	_	4.2	_	pF	
Collector-emitter of	on resistance	Ron	$I_B = -1 \text{ mA}, V_{in} = -1 V_{rms}, f = 1 \text{ kHz}$	_	0.9	_	Ω	
Switching time Storage time Fall time	t _{on}	OUTPUT 300Ω OUTPUT		40				
	t _{stg}	$10\mu \mathrm{s}$ V_{BB} V_{CC}	_	280	_	ns		
	Fall time	t _f	$=3V=-6V$ $I_{B1}=-I_{B2}=5 \text{ mA}$	C	45			
Note: h _{FE} class	sification A: 300~	600, B: 500~1						

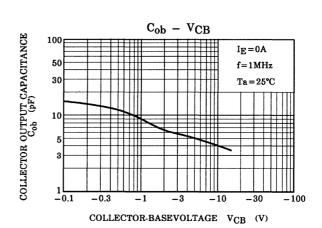




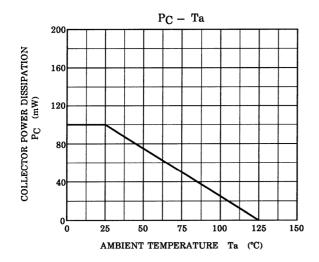








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20070701-EN GENERAL

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